

FDFMA2N028Z

Integrated N-Channel PowerTrench® MOSFET and Schottky Diode

20V, 3.7A, 68mΩ

Features

MOSFET

- Max $r_{DS(on)}$ = 68mΩ at $V_{GS} = 4.5V$, $I_D = 3.7A$
- Max $r_{DS(on)}$ = 86mΩ at $V_{GS} = 2.5V$, $I_D = 3.3A$
- HBM ESD protection level > 2kV (Note 3)

Schottky

- $V_F < 0.37V$ @ 500mA
- Low profile - 0.8 mm maximum - in the new package MicroFET 2x2 mm
- RoHS Compliant



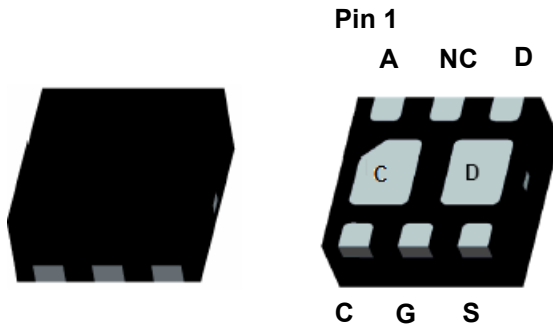
General Description

This device is designed specifically as a single package solution for a boost topology in cellular handset and other ultra-portable applications. It features a MOSFET with low on-state resistance, and an independently connected schottky diode with low forward voltage.

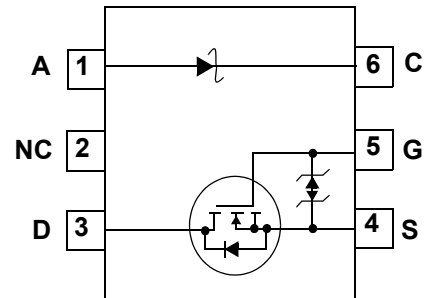
The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to switching and linear mode applications.

Application

- DC - DC Conversion



MicroFET 2X2



MOSFET Maximum Ratings $T_J = 25^\circ C$ unless otherwise noted

| Symbol | Parameter | Rated | Units |
|----------------|--|-------------|------------|
| V_{DS} | Drain to Source Voltage | 20 | V |
| V_{GS} | Gate to Source Voltage | ± 12 | V |
| I_D | Drain Current -Continuous (Note 1a) | 3.7 | A |
| | -Pulsed | 6 | |
| P_D | Power Dissipation (Note 1a) | 1.4 | W |
| | Power Dissipation (Note 1b) | 0.7 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ C$ |
| V_{RR} | Schottky Repetitive Peak Reverse Voltage | 20 | V |
| I_O | Schottky Average Forward Current | 2 | A |

Thermal Characteristics

| | | | |
|-----------------|---|-----|--------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 86 | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1b) | 173 | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1c) | 86 | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1d) | 140 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-------------|--------------|-----------|------------|------------|
| .N28 | FDFMA2N028Z | MicroFET 2X2 | 7" | 8mm | 3000 units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|----|----|----------|----------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 20 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | 15 | | $\text{mV}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$ | | | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$ | | | ± 10 | μA |

On Characteristics

| | | | | | | |
|--|--|--|-----|-----|-----|----------------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 0.6 | 1.0 | 1.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | -4 | | $\text{mV}/^\circ\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 4.5\text{V}, I_D = 3.7\text{A}$ | | 37 | 68 | $\text{m}\Omega$ |
| | | $V_{GS} = 2.5\text{V}, I_D = 3.3\text{A}$ | | 50 | 86 | |
| | | $V_{GS} = 4.5\text{V}, I_D = 3.7\text{A}, T_J = 125^\circ\text{C}$ | | 53 | 90 | |
| g_{FS} | Forward Trans conductance | $V_{DS} = 10\text{V}, I_D = 3.7\text{A}$ | | 16 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|-----|-----|-------------|
| C_{iss} | Input Capacitance | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$ | | 340 | 455 | pF |
| C_{oss} | Output Capacitance | | | 80 | 110 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 60 | 90 | pF |

Switching Characteristics

| | | | | | | |
|--------------|-------------------------------|---|--|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 10\text{V}, I_D = 1\text{A}$ $V_{GS} = 4.5\text{V}, R_{GEN} = 6\Omega$ | | 8 | 16 | ns |
| t_r | Rise Time | | | 8 | 16 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 14 | 26 | ns |
| t_f | Fall Time | | | 3 | 6 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge | | $V_{DS} = 10\text{V}, I_D = 3.7\text{A}$ | | 4 | 6 |
| Q_{gs} | Gate to Source Gate Charge | $V_{GS} = 4.5\text{V}$ | | 0.7 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | 1.1 | | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|---|--|--|-----|-----|----|
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | | 1.1 | A |
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = 1.1\text{A}$ (Note 2) | | 0.7 | 1.2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 3.7\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 11 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 2 | | nC |

Schottky Diode Characteristics

| | | | | | | | |
|-------|-----------------|----------------------|---------------------------|----|------|-------|---------------|
| V_R | Reverse Voltage | $I_R = 1\text{mA}$ | $T_J = 25^\circ\text{C}$ | 20 | | | V |
| I_R | Reverse Leakage | $V_R = 20\text{V}$ | $T_J = 25^\circ\text{C}$ | | 30 | 300 | μA |
| | | | $T_J = 125^\circ\text{C}$ | | 10 | 45 | mA |
| V_F | Forward Voltage | $I_F = 500\text{mA}$ | $T_J = 25^\circ\text{C}$ | | 0.32 | 0.37 | V |
| | | | $T_J = 125^\circ\text{C}$ | | 0.21 | 0.26 | |
| | | $I_F = 1\text{A}$ | $T_J = 25^\circ\text{C}$ | | 0.37 | 0.435 | |
| | | | $T_J = 125^\circ\text{C}$ | | 0.28 | 0.33 | |

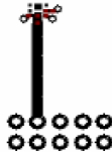
Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Notes:

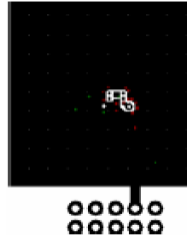
- 1: $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz. copper pad on a 1.5×1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
 - (a) MOSFET $R_{\theta JA} = 86^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2 oz copper, $1.5'' \times 1.5'' \times 0.062''$ thick PCB.
 - (b) MOSFET $R_{\theta JA} = 173^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.
 - (c) Schottky $R_{\theta JA} = 86^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2 oz copper, $1.5'' \times 1.5'' \times 0.062''$ thick PCB.
 - (d) Schottky $R_{\theta JA} = 140^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.



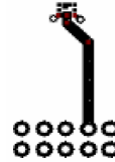
a) 86°C/W when mounted on a 1in^2 pad of 2 oz copper.



b) 173°C/W when mounted on a minimum pad of 2 oz copper.



c) 86°C/W when mounted on a 1in^2 pad of 2 oz copper.



d) 140°C/W when mounted on a minimum pad of 2 oz copper.

2: Pulse Test: Pulse Width $< 300\mu\text{s}$, Duty cycle $< 2.0\%$.

3: The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

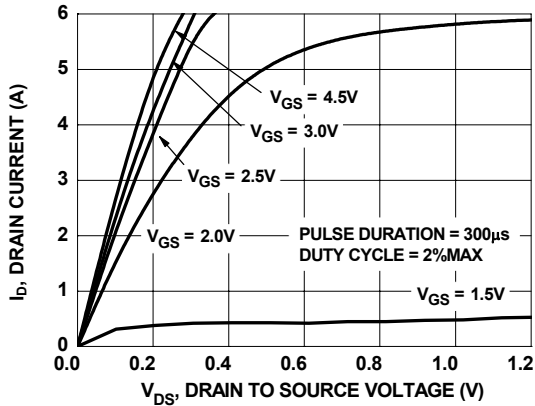


Figure 1. On-Region Characteristics

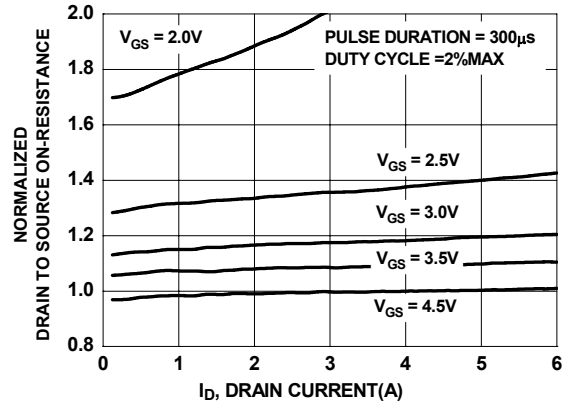


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

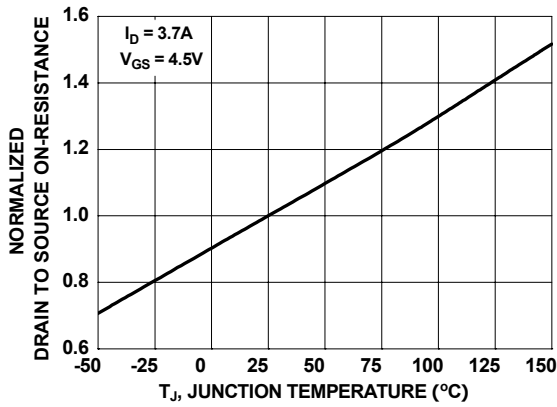


Figure 3. Normalized On-Resistance vs Junction Temperature

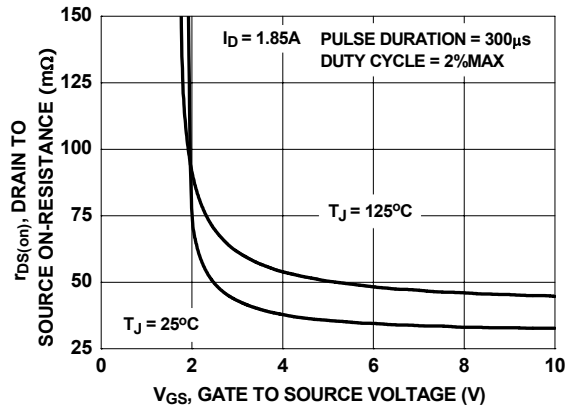


Figure 4. On-Resistance vs Gate to Source Voltage

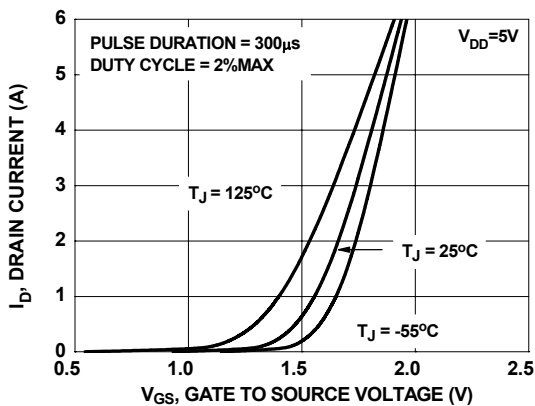


Figure 5. Transfer Characteristics

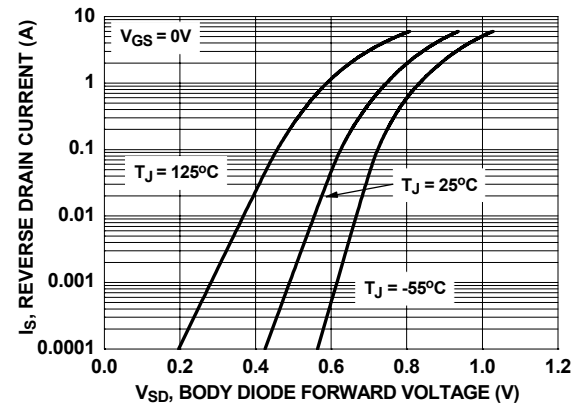


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

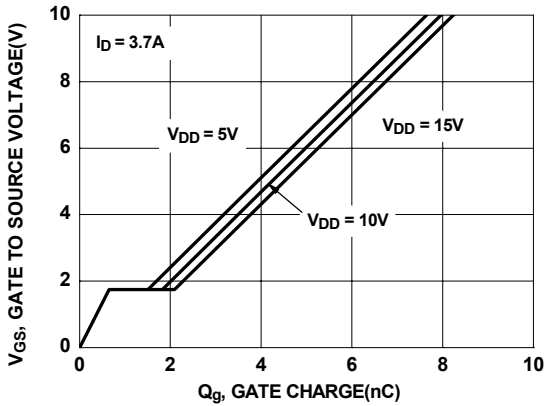


Figure 7. Gate Charge Characteristics

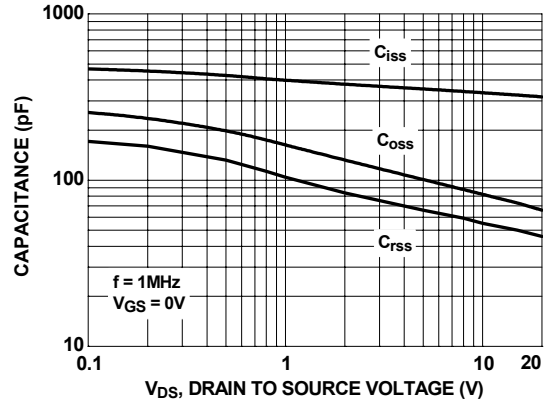


Figure 8. Capacitance Characteristics

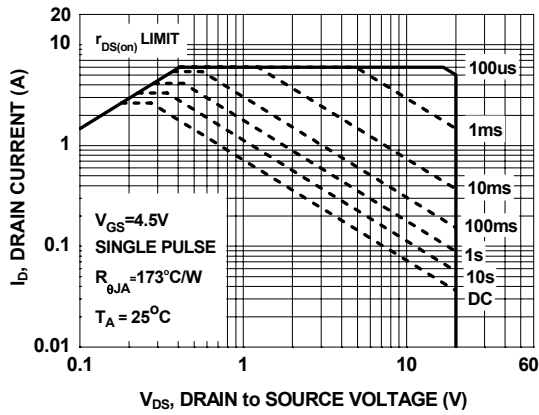


Figure 9. Forward Bias Safe Operating Area

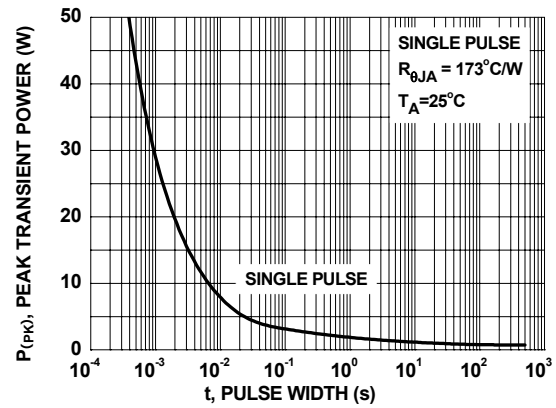


Figure 10. Single Pulse Maximum Power Dissipation

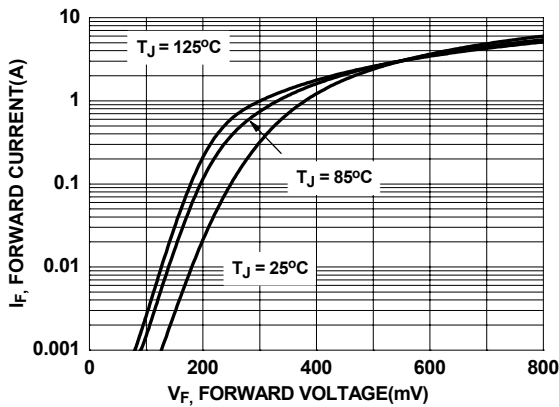


Figure 11. Schottky Diode Forward Current

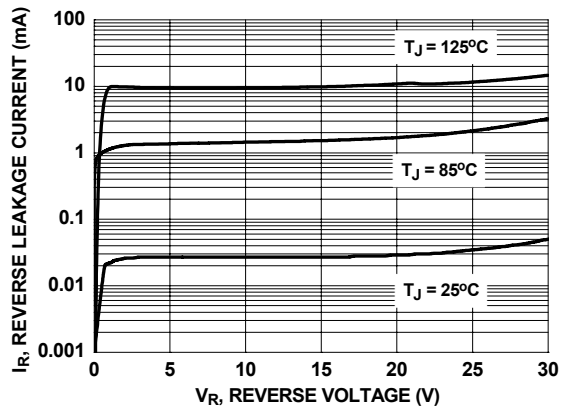
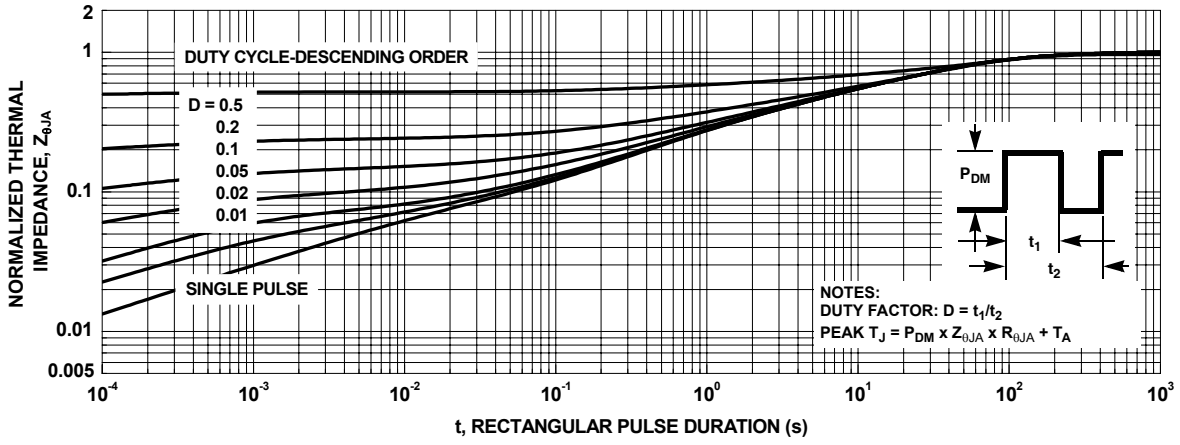
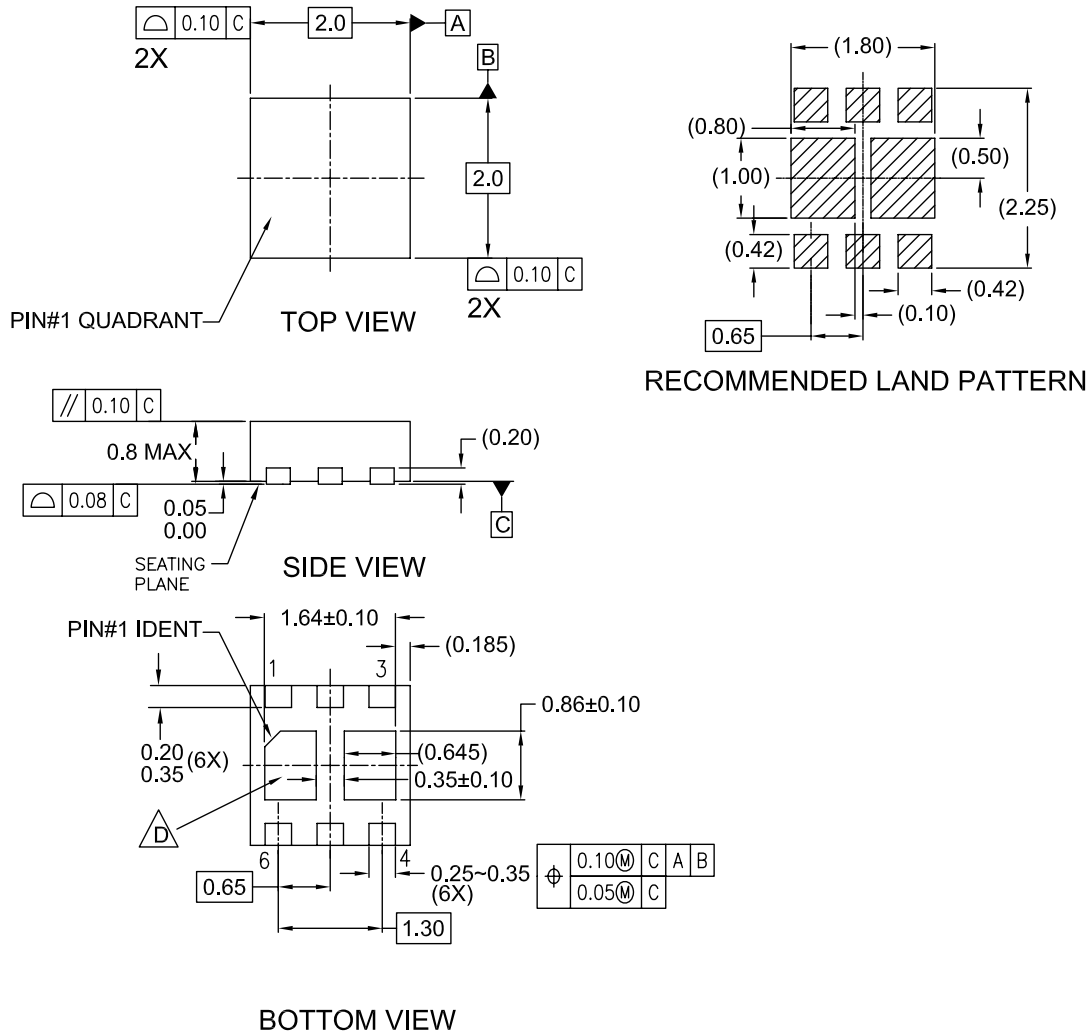


Figure 12. Schottky Diode Reverse Current


Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



Dimensional Outline and Pad Layout








NOTES:

- A. CONFORMS TO JEDEC REGISTRATION MO-229, VARIATION VCCC EXCEPT AS NOTED.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
-  NON-JEDEC DUAL DAP
- E. DRAWING FILE NAME : MLP06Jrev3



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